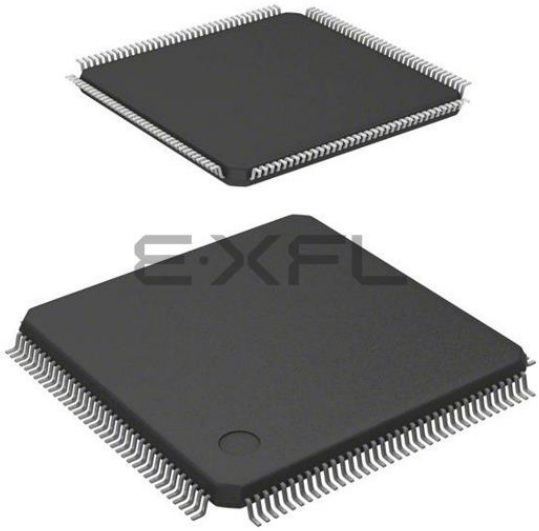

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	121
Program Memory Size	768KB (768K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 53x10/12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560b54l5c6e0x

1 Introduction

1.1 Document overview

This document describes the features of the family and options available within the family members, and highlights important electrical and physical characteristics of the device.

1.2 Description

This family of 32-bit system-on-chip (SoC) microcontrollers is the latest achievement in integrated automotive application controllers. It belongs to an expanding family of automotive-focused products designed to address the next wave of body electronics applications within the vehicle.

The advanced and cost-efficient e200z0h host processor core of this automotive controller family complies with the Power Architecture technology and only implements the VLE (variable-length encoding) APU (Auxiliary Processor Unit), providing improved code density. It operates at speeds of up to 64 MHz and offers high performance processing optimized for low power consumption. It capitalizes on the available development infrastructure of current Power Architecture devices and is supported with software drivers, operating systems and configuration code to assist with users implementations.

Table 2. SPC560B54/6x family comparison(1)

Feature	SPC560B54		SPC560B60			SPC560B64			
CPU	e200z0h								
Execution speed(2)	Up to 64 MHz								
Code flash memory	768 KB		1 MB			1.5 MB			
Data flash memory	64 (4 × 16) KB								
SRAM	64 KB		80 KB			96 KB			
MPU	8-entry								
eDMA	16 ch								
10-bit ADC	Yes								
dedicated(3)	7 ch	15 ch	7 ch	15 ch	29 ch	7 ch	15 ch	29 ch	29 ch
shared with 12-bit ADC	19 ch								
12-bit ADC	Yes								
dedicated(4)	5 ch								
shared with 10-bit ADC	19 ch								
Total timer I/O(5) eMIOS	37 ch, 16-bit	64 ch, 16-bit	37 ch, 16-bit	64 ch, 16-bit	64 ch, 16-bit	37 ch, 16-bit	64 ch,16-bit	64 ch, 16-bit	64 ch, 16-bit
Counter / OPWM / ICOC(6)	10 ch								
O(I)PWM / OPWFMB / OPWMCB / ICOC(7)	7 ch								
O(I)PWM / ICOC(8)	7 ch	14 ch	7 ch	14 ch	14 ch	7 ch	14 ch	14 ch	14 ch

Figure 4. LQFP100 pin configuration

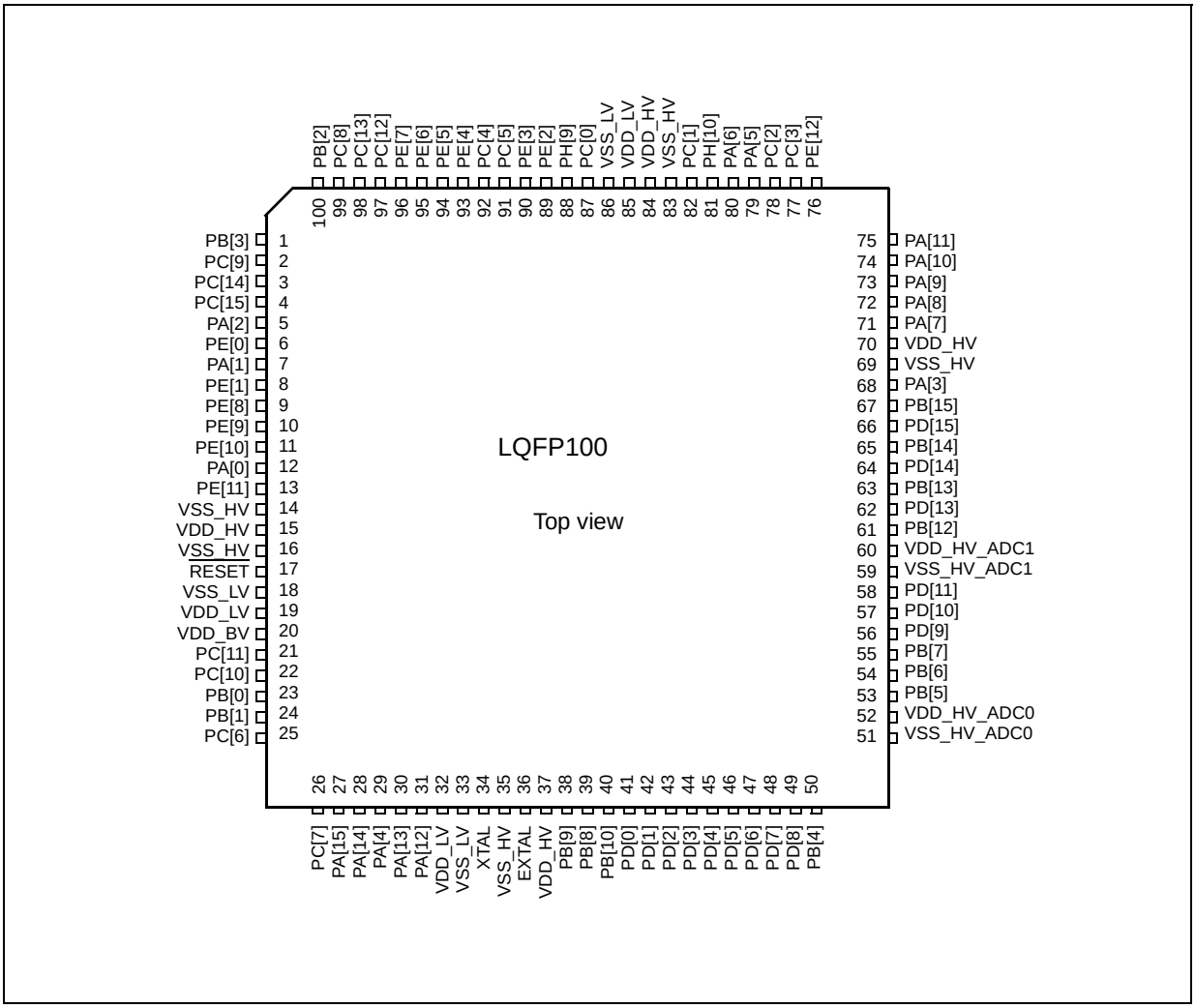


Figure 5 shows the SPC560B54/6x in the LBGA208 package.

Table 4. Voltage supply pin descriptions (continued)

Port pin	Function	Pin number			
		LQFP100	LQFP144	LQFP176	LBGA208
VDD_BV	Internal regulator supply voltage	20	24	32	K3
VSS_HV_ADC0	Reference ground and analog ground for the A/D converter 0 (10-bit)	51	73	89	R15
VDD_HV_ADC0	Reference voltage and analog supply for the A/D converter 0 (10-bit)	52	74	90	P14
VSS_HV_ADC1	Reference ground and analog ground for the A/D converter 1 (12-bit)	59	81	98	N12
VDD_HV_ADC1	Reference voltage and analog supply for the A/D converter 1 (12-bit)	60	82	99	K13

1. A decoupling capacitor must be placed between each of the three VDD_LV/VSS_LV supply pairs to ensure stable voltage (see the recommended operating conditions in the device datasheet).

3.5 Pad types

In the device the following types of pads are available for system pins and functional port pins:

S = Slow[d]

M = Medium[d] [e]

F = Fast[d] [e]

I = Input only with analog feature[d]

J = Input/Output ('S' pad) with analog feature

X = Oscillator

3.6 System pins

The system pins are listed in *Table 5*.

d. See the I/O pad electrical characteristics in the chip datasheet for details.

e. All medium and fast pads are in slow configuration by default at reset and can be configured as fast or medium. The only exception is PC[1] which is in medium configuration by default (see the PCR.SRC description in the chip reference manual, Pad Configuration Registers (PCR0–PCR148)).

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration[3]	Pin number			
								LQFP 100	LQFP 144	LQFP 176	LBGA 208[4]
PB[1]	PCR[17]	AF0 AF1 AF2 AF3 — — —	GPIO[17] — E0UC[31] — WKPU[4][5] CAN0RX LIN0RX	SIUL — eMIOS_0 — WKPU FlexCAN_0 LINFlex_0	I/O — I/O — I I I	S	Tristate	24	32	40	N1
PB[2]	PCR[18]	AF0 AF1 AF2 AF3	GPIO[18] LIN0TX SDA E0UC[30]	SIUL LINFlex_0 I^2C_0 eMIOS_0	I/O O I/O I/O	M	Tristate	100	144	176	B2
PB[3]	PCR[19]	AF0 AF1 AF2 AF3 — —	GPIO[19] E0UC[31] SCL — WKPU[11][5] LIN0RX	SIUL eMIOS_0 I^2C_0 — WKPU LINFlex_0	I/O I/O I/O — I I	S	Tristate	1	1	1	C3
PB[4]	PCR[20]	AF0 AF1 AF2 AF3 — — —	— — — — ADC0_P[0] ADC1_P[0] GPIO[20]	— — — — ADC_0 ADC_1 SIUL	— — — — I I I	I	Tristate	50	72	88	T16

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration[3]	Pin number			
								LQFP 100	LQFP 144	LQFP 176	LBGA 208[4]
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 — —	GPIO[56] — — — ADC0_P[12] ADC1_P[12]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	49	71	87	T15
PD[9]	PCR[57]	AF0 AF1 AF2 AF3 — —	GPIO[57] — — — ADC0_P[13] ADC1_P[13]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	56	78	94	N15
PD[10]	PCR[58]	AF0 AF1 AF2 AF3 — —	GPIO[58] — — — ADC0_P[14] ADC1_P[14]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	57	79	95	N14
PD[11]	PCR[59]	AF0 AF1 AF2 AF3 — —	GPIO[59] — — — ADC0_P[15] ADC1_P[15]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	58	80	96	N16

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration[3]	Pin number			
								LQFP 100	LQFP 144	LQFP 176	LBGA 208[4]
PD[12]	PCR[60]	AF0 AF1 AF2 AF3 —	GPIO[60] CS5_0 E0UC[24] — ADC0_S[4]	SIUL DSPI_0 eMIOS_0 — ADC_0	I/O O I/O — I	J	Tristate	—	—	100	M15
PD[13]	PCR[61]	AF0 AF1 AF2 AF3 —	GPIO[61] CS0_1 E0UC[25] — ADC0_S[5]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O I/O I/O — I	J	Tristate	62	84	102	M14
PD[14]	PCR[62]	AF0 AF1 AF2 AF3 —	GPIO[62] CS1_1 E0UC[26] — ADC0_S[6]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O O I/O — I	J	Tristate	64	86	104	L15
PD[15]	PCR[63]	AF0 AF1 AF2 AF3 —	GPIO[63] CS2_1 E0UC[27] — ADC0_S[7]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O O I/O — I	J	Tristate	66	88	106	L14
Port E											

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration[3]	Pin number			
								LQFP 100	LQFP 144	LQFP 176	LBGA 208[4]
PE[0]	PCR[64]	AF0 AF1 AF2 AF3 — —	GPIO[64] E0UC[16] — — WKPU[6][5] CAN5RX	SIUL eMIOS_0 — — WKPU FlexCAN_5	I/O I/O — — I I	S	Tristate	6	10	18	F1
PE[1]	PCR[65]	AF0 AF1 AF2 AF3	GPIO[65] E0UC[17] CAN5TX —	SIUL eMIOS_0 FlexCAN_5 —	I/O I/O O —	M	Tristate	8	12	20	F4
PE[2]	PCR[66]	AF0 AF1 AF2 AF3 — —	GPIO[66] E0UC[18] — — EIRQ[21] SIN_1	SIUL eMIOS_0 — — SIUL DSPI_1	I/O I/O — — I I	M	Tristate	89	128	156	D7
PE[3]	PCR[67]	AF0 AF1 AF2 AF3	GPIO[67] E0UC[19] SOUT_1 —	SIUL eMIOS_0 DSPI_1 —	I/O I/O O —	M	Tristate	90	129	157	C7
PE[4]	PCR[68]	AF0 AF1 AF2 AF3 —	GPIO[68] E0UC[20] SCK_1 — EIRQ[9]	SIUL eMIOS_0 DSPI_1 — SIUL	I/O I/O I/O — I	M	Tristate	93	132	160	D6

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration[3]	Pin number			
								LQFP 100	LQFP 144	LQFP 176	LBGA 208[4]
PJ[2]	PCR[146]	AF0 AF1 AF2 AF3 —	GPIO[146] CS0_5 — — ADC0_S[26]	SIUL DSPI_5 — — ADC_0	I/O I/O — — I	J	Tristate	—	—	72	P4
PJ[3]	PCR[147]	AF0 AF1 AF2 AF3 —	GPIO[147] CS1_5 — — ADC0_S[27]	SIUL DSPI_5 — — ADC_0	I/O O — — I	J	Tristate	—	—	71	P2
PJ[4]	PCR[148]	AF0 AF1 AF2 AF3	GPIO[148] SCK_5 E1UC[18] —	SIUL DSPI_5 eMIOS_1 —	I/O I/O I/O —	M	Tristate	—	—	5	A4

1. Alternate functions are chosen by setting the values of the PCR.PA bitfields inside the SIUL module. PCR.PA = 00 → AF0; PCR.PA = 01 → AF1; PCR.PA = 10 → AF2; PCR.PA = 11 → AF2. This is intended to select the output functions; to use one of the input functions, the PCR.IBE bit must be written to '1', regardless of the values selected in the PCR.PA bitfields. For this reason, the value corresponding to an input only function is reported as "—".
2. Multiple inputs are routed to all respective modules internally. The input of some modules must be configured by setting the values of the PSMIO.PADSELx bitfields inside the SIUL module.
3. The RESET configuration applies during and after reset.
4. LBGA208 available only as development package for Nexus2+
5. All WKPU pins also support external interrupt capability. See the WKPU chapter for further details.
6. NMI has higher priority than alternate function. When NMI is selected, the PCR.AF field is ignored.
7. "Not applicable" because these functions are available only while the device is booting. Refer to the BAM information for details.
8. Value of PCR.IBE bit must be 0.
9. This wakeup input cannot be used to exit STANDBY mode.

3.8 Nexus 2+ pins

In the LBGA208 package, eight additional debug pins are available (see *Table 7*).

Table 7. Nexus 2+ pin descriptions

Port pin	Function	I/O direction	Pad type	Function after reset	Pin number		
					LQFP 100	LQFP 144	LBGA 208(1)
MCKO	Message clock out	O	F	—	—	—	T4
MDO0	Message data out 0	O	M	—	—	—	H15
MDO1	Message data out 1	O	M	—	—	—	H16
MDO2	Message data out 2	O	M	—	—	—	H14
MDO3	Message data out 3	O	M	—	—	—	H13
EVTI	Event in	I	M	Pull-up	—	—	K1
EVTO	Event out	O	M	—	—	—	L4
MSEO	Message start/end out	O	M	—	—	—	G16

1. LBGA208 available only as development package for Nexus2+.

4 Electrical characteristics

This section contains electrical characteristics of the device as well as temperature and power considerations.

This product contains devices to protect the inputs against damage due to high static voltages. However, it is advisable to take precautions to avoid application of any voltage higher than the specified maximum rated voltages.

To enhance reliability, unused inputs can be driven to an appropriate logic voltage level (V_{DD} or V_{SS}). This could be done by the internal pull-up and pull-down, which is provided by the product for most general purpose pins.

The parameters listed in the following tables represent the characteristics of the device and its demands on the system.

In the tables where the device logic provides signals with their respective timing characteristics, the symbol “CC” for Controller Characteristics is included in the Symbol column.

In the tables where the external system must provide signals with their respective timing characteristics to the device, the symbol “SR” for System Requirement is included in the Symbol column.

4.1 Parameter classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the classifications listed in *Table 8* are used and the parameters are tagged accordingly in the tables where appropriate.

Table 8. Parameter classifications

Classification tag	Tag description
P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

Note: The classification is shown in the column labeled “C” in the parameter tables where appropriate.

4.2 NVUSRO register

Bit values in the Non-Volatile User Options (NVUSRO) Register control portions of the device configuration, namely electrical parameters such as high voltage supply and oscillator margin, as well as digital functionality (watchdog enable/disable after reset).

Table 15. LQFP thermal characteristics[1] (continued)

Symbol		C	Parameter	Conditions[2]	Pin count	Value			Unit
						Min	Typ	Max	
$R_{\theta JB}$	CC		Thermal resistance, junction-to-board[4]	Single-layer board — 1s	100	—	—	36	°C/W
					144	—	—	38	
					176	—	—	38	
				Four-layer board — 2s2p	100	—	—	33.6	
					144	—	—	33.4	
					176	—	—	33.4	
$R_{\theta JC}$	CC		Thermal resistance, junction-to-case[5]	Single-layer board — 1s	100	—	—	23	°C/W
					144	—	—	23	
					176	—	—	23	
				Four-layer board — 2s2p	100	—	—	19.8	
					144	—	—	19.2	
					176	—	—	18.8	

1. Thermal characteristics are targets based on simulation.
2. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C.
3. Junction-to-ambient thermal resistance determined per JEDEC JESD51-3 and JESD51-6. Thermal test board meets JEDEC specification for this package. When Greek letters are not available, the symbols are typed as R_{thJA} and R_{thJMA}.
4. Junction-to-board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package. When Greek letters are not available, the symbols are typed as R_{thJB}.
5. Junction-to-case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer. When Greek letters are not available, the symbols are typed as R_{thJC}.

4.5.3 Power considerations

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using *Equation 1*:

Equation 1 $T_J = T_A + (P_D \times R_{\theta JA})$

Where:

T_A is the ambient temperature in °C.

$R_{\theta JA}$ is the package junction-to-ambient thermal resistance, in °C/W.

P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$).

P_{INT} is the product of I_{DD} and V_{DD}, expressed in watts. This is the chip internal power.

$P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications, $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant, if the device is configured to continuously drive external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

Table 21. Output pin transition times (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
t_{tr}	CC	D	Output transition time output pin[2] MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 SIUL.PCRx.SRC = 1	—	—	10	ns
		T		C_L = 50 pF		—	—	20	
		D		C_L = 100 pF		—	—	40	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 SIUL.PCRx.SRC = 1	—	—	12	
		T		C_L = 50 pF		—	—	25	
		D		C_L = 100 pF		—	—	40	
t_{tr}	CC	D	Output transition time output pin[2] FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	4	ns
				C_L = 50 pF		—	—	6	
				C_L = 100 pF		—	—	12	
				C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	4	
				C_L = 50 pF		—	—	7	
				C_L = 100 pF		—	—	12	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. C_L includes device and package capacitances (C_{PKG} < 5 pF).

4.6.5 I/O pad current specification

The I/O pads are distributed across the I/O supply segment. Each I/O supply segment is associated to a V_{DD}/V_{SS} supply pair as described in *Table 22*.

Table 23 provides I/O consumption figures.

In order to ensure device reliability, the average current of the I/O on a single segment should remain below the I_{AVGSEG} maximum value.

Table 22. I/O supply segments

Package	Supply segment							
	1	2	3	4	5	6	7	8
LBGA208 (1)	Equivalent to LQFP176 segment pad distribution						MCKO	MDOn /MSEO
LQFP176	pin7 – pin27	pin28 – pin57	pin59 – pin85	pin86 – pin123	pin124 – pin150	pin151 – pin6	—	—
LQFP144	pin20 – pin49	pin51 – pin99	pin100 – pin122	pin 123 – pin19	—	—	—	—
LQFP100	pin16 – pin35	pin37 – pin69	pin70 – pin83	pin84 – pin15	—	—	—	—

1. LBGA208 available only as development package for Nexus2+.

Table 24. I/O weight[1] (continued)

Supply segment			Pad	LQFP176				LQFP144/100			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
LQFP 176	LQFP 144	LQFP 100		SRC[2] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
6	4	4	PC[0]	6%	9%	7%	8%	7%	10%	8%	8%
			PH[9]	7%	—	8%	—	7%	—	9%	—
			PE[2]	7%	10%	8%	9%	8%	11%	9%	10%
			PE[3]	7%	10%	9%	9%	8%	12%	10%	10%
			PC[5]	7%	11%	9%	9%	8%	12%	10%	11%
			PC[4]	8%	11%	9%	10%	9%	13%	10%	11%
			PE[4]	8%	11%	9%	10%	9%	13%	11%	12%
			PE[5]	8%	11%	10%	10%	9%	14%	11%	12%
		—	PH[4]	8%	12%	10%	10%	10%	14%	12%	12%
		—	PH[5]	8%	—	10%	—	10%	—	12%	—
		—	PH[6]	8%	12%	10%	11%	10%	15%	12%	13%
		—	PH[7]	9%	12%	10%	11%	11%	15%	13%	13%
		—	PH[8]	9%	12%	10%	11%	11%	16%	13%	14%
		4	PE[6]	9%	12%	10%	11%	11%	16%	13%	14%
			PE[7]	9%	12%	10%	11%	11%	16%	14%	14%
	—	—	PI[3]	9%	—	10%	—	—	—	—	—
	—	—	PI[2]	9%	—	10%	—	—	—	—	—
	—	—	PI[1]	9%	—	10%	—	—	—	—	—
	—	—	PI[0]	9%	—	10%	—	—	—	—	—
	4	4	PC[12]	8%	12%	10%	11%	12%	18%	15%	16%
			PC[13]	8%	—	10%	—	13%	—	15%	—
			PC[8]	8%	—	10%	—	13%	—	15%	—
			PB[2]	8%	11%	9%	10%	13%	18%	15%	16%

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. SRC: “Slew Rate Control” bit in SIU_PCRx.

4.7 $\overline{\text{RESET}}$ electrical characteristics

The device implements a dedicated bidirectional $\overline{\text{RESET}}$ pin.

The internal voltage regulator requires external capacitance (C_{REGn}) to be connected to the device in order to provide a stable low voltage digital supply to the device. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the board to less than 5 nH.

Each decoupling capacitor must be placed between each of the three V_{DD_LV}/V_{SS_LV} supply pairs to ensure stable voltage (see *Section 4.4: Recommended operating conditions*).

Table 26. Voltage regulator electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
C_{REGn}	SR	—	Internal voltage regulator external capacitance	—	200	—	500	nF
R_{REG}	SR	—	Stability capacitor equivalent serial resistance	Range: 10 kHz to 20 MHz	—	—	0.2	W
C_{DEC1}	SR	—	Decoupling capacitance[2] ballast	V_{DD_BV}/V_{SS_LV} pair: V_{DD_BV} = 4.5 V to 5.5 V	100[3]	470[4]	—	nF
				V_{DD_BV}/V_{SS_LV} pair: V_{DD_BV} = 3 V to 3.6 V	400		—	
C_{DEC2}	SR	—	Decoupling capacitance regulator supply	V_{DD}/V_{SS} pair	10	100	—	nF
V_{MREG}	CC	T	Main regulator output voltage	Before exiting from reset	—	1.32	—	V
		P		After trimming	1.16	1.28	—	
I_{MREG}	SR	—	Main regulator current provided to V_{DD_LV} domain	—	—	—	150	mA
$I_{MREGINT}$	CC	D	Main regulator module current consumption	I_{MREG} = 200 mA	—	—	2	mA
				I_{MREG} = 0 mA	—	—	1	
V_{LPREG}	CC	P	Low-power regulator output voltage	After trimming	1.16	1.28	—	V
I_{LPREG}	SR	—	Low-power regulator current provided to V_{DD_LV} domain	—	—	—	15	mA
$I_{LPREGINT}$	CC	D	Low-power regulator module current consumption	I_{LPREG} = 15 mA; T_A = 55 °C	—	—	600	µA
		—		I_{LPREG} = 0 mA; T_A = 55 °C	—	5	—	
V_{ULPREG}	CC	P	Ultra low power regulator output voltage	After trimming	1.16	1.28	—	V
I_{ULPREG}	SR	—	Ultra low power regulator current provided to V_{DD_LV} domain	—	—	—	5	mA
$I_{ULPREGINT}$	CC	D	Ultra low power regulator module current consumption	I_{ULPREG} = 5 mA; T_A = 55 °C	—	—	100	µA
				I_{ULPREG} = 0 mA; T_A = 55 °C	—	2	—	
I_{DD_BV}	CC	D	In-rush average current on V_{DD_BV} during power-up[5]	—	—	—	300[6]	mA

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. This capacitance value is driven by the constraints of the external voltage regulator supplying the V_{DD_BV} voltage. A typical value is in the range of 470 nF.
3. This value is acceptable to guarantee operation from 4.5 V to 5.5 V.
4. External regulator and capacitance circuitry must be capable of providing I_{DD_BV} while maintaining supply V_{DD_BV} in operating range.
5. In-rush average current is seen only for short time during power-up and on standby exit (maximum 20 µs, depending on external capacitances to be loaded).
6. The duration of the in-rush current depends on the capacitance placed on LV pins. BV decoupling capacitors must be sized accordingly. Refer to I_{MREG} value for minimum amount of current to be provided in cc.

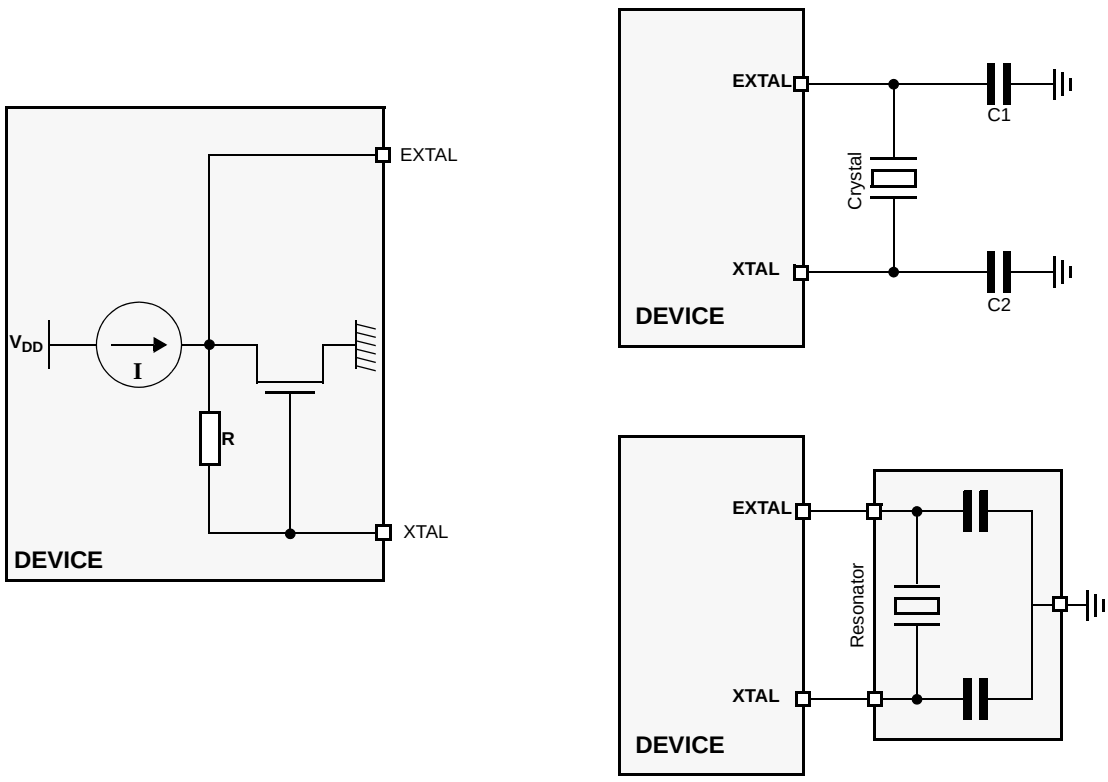
4.8.2 Low voltage detector electrical characteristics

The device implements a power-on reset (POR) module to ensure correct power-up initialization, as well as five low voltage detectors (LVDs) to monitor the V_{DD} and the V_{DD_LV} voltage while device is supplied:

- POR monitors V_{DD} during the power-up phase to ensure device is maintained in a safe reset state (refer to RGM Destructive Event Status (RGM_DES) Register flag F_POR in device reference manual)
- LVDHV3 monitors V_{DD} to ensure device reset below minimum functional supply (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD27 in device reference manual)
- LVDHV3B monitors V_{DD_BV} to ensure device reset below minimum functional supply (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD27_VREG in device reference manual)
- LVDHV5 monitors V_{DD} when application uses device in the 5.0 V ± 10% range (refer to RGM Functional Event Status (RGM_FES) Register flag F_LVD45 in device reference manual)
- LVDLVCOR monitors power domain No. 1 (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD12_PD1 in device reference manual)
- LVDLVBKP monitors power domain No. 0 (refer to RGM Destructive Event Status (RGM_DES) Register flag F_LVD12_PD0 in device reference manual)

Note: When enabled, power domain No. 2 is monitored through LVDLVBKP.

Figure 11. Crystal oscillator and resonator connection scheme



Notes:
1. XTAL/EXTAL must not be directly used to drive external circuits
2. A series resistor may be required, according to crystal oscillator supplier recommendations.

Table 37. Crystal description

Nominal frequency (MHz)	NDK crystal reference	Crystal equivalent series resistance ESR Ω	Crystal motional capacitance (C_m) fF	Crystal motional inductance (L_m) mH	Load on xtalin/xtalout C1 = C2 (pF)(1)	Shunt capacitance between xtalout and xtalin C0(2) (pF)
4	NX8045GB	300	2.68	591.0	21	2.93
8	NX5032GA	300	2.46	160.7	17	3.01
10		150	2.93	86.6	15	2.91
12		120	3.11	56.5	15	2.93
16		120	3.90	25.3	10	3.00

1. The values specified for C1 and C2 are the same as used in simulations. It should be ensured that the testing includes all the parasitics (from the board, probe, crystal, etc.) as the AC / transient behavior depends upon them.
2. The value of C0 specified here includes 2 pF additional capacitance for parasitics (to be seen with bond-pads, package, etc.).

Table 43. Slow internal RC oscillator (128 kHz) electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
$\Delta_{SIRCPRE}$	CC	C	Slow internal RC oscillator precision after software trimming of f_{SIRC}	T_A = 25 °C	–2	—	2	%
$\Delta_{SIRCTRIM}$	CC	C	Slow internal RC oscillator trimming step	—	—	2.7	—	
$\Delta_{SIRCVAR}$	CC	C	Slow internal RC oscillator variation in temperature and supply with respect to f_{SIRC} at T_A = 55 °C in high frequency configuration	High frequency configuration	–10	—	10	%

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. This does not include consumption linked to clock tree toggling and peripherals consumption when RC oscillator is ON.

4.17 ADC electrical characteristics

4.17.1 Introduction

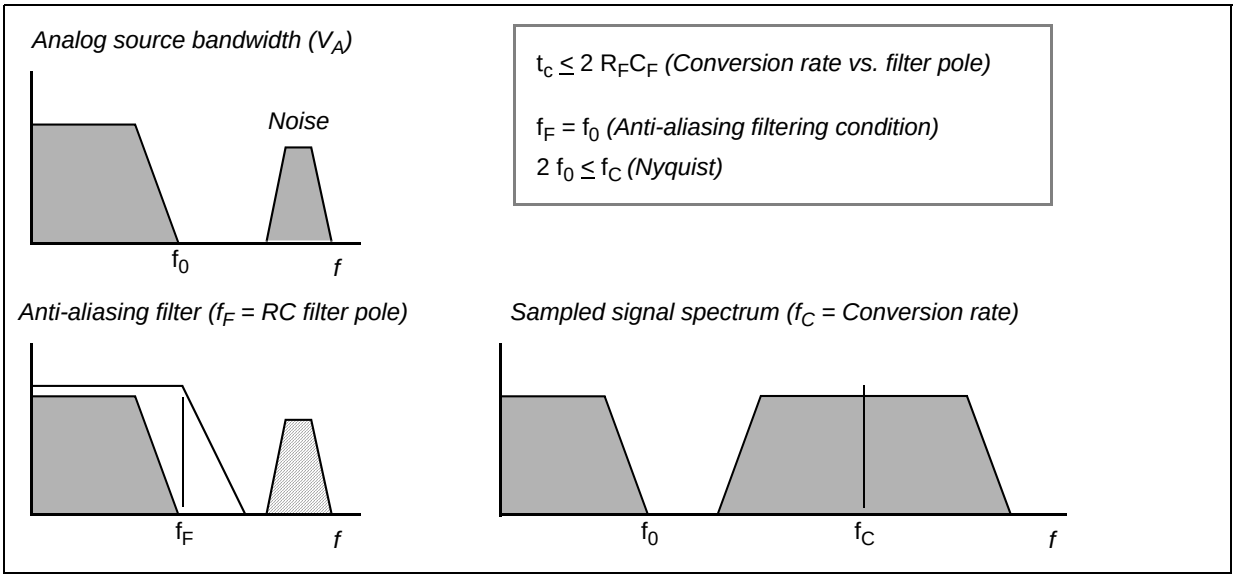
The device provides two Successive Approximation Register (SAR) analog-to-digital converters (10-bit and 12-bit).

Equation 11

$$V_{A2} \bullet (C_S + C_{P1} + C_{P2} + C_F) = V_A \bullet C_F + V_{A1} \bullet (C_{P1} + C_{P2} + C_S)$$

The two transients above are not influenced by the voltage source that, due to the presence of the $R_F C_F$ filter, is not able to provide the extra charge to compensate the voltage drop on C_S with respect to the ideal source V_A; the time constant $R_F C_F$ of the filter is very high with respect to the sampling time (t_s). The filter is typically designed to act as antialiasing.

Figure 20. Spectral representation of input signal



Calling f_0 the bandwidth of the source signal (and as a consequence the cut-off frequency of the antialiasing filter, f_F), according to the Nyquist theorem the conversion rate f_C must be at least $2f_0$; it means that the constant time of the filter is greater than or at least equal to twice the conversion period (t_c). Again the conversion period t_c is longer than the sampling time t_s, which is just a portion of it, even when fixed channel continuous conversion mode is selected (fastest conversion rate at a specific channel): in conclusion it is evident that the time constant of the filter $R_F C_F$ is definitively much higher than the sampling time t_s, so the charge level on C_S cannot be modified by the analog signal source during the time in which the sampling switch is closed.

The considerations above lead to impose new constraints on the external circuit, to reduce the accuracy error due to the voltage drop on C_S; from the two charge balance equations above, it is simple to derive *Equation 12* between the ideal and real sampled voltage on C_S:

Equation 12

$$\frac{V_{A2}}{V_A} = \frac{C_{P1} + C_{P2} + C_F}{C_{P1} + C_{P2} + C_F + C_S}$$

From this formula, in the worst case (when V_A is maximum, that is for instance 5 V), assuming to accept a maximum error of half a count, a constraint is evident on C_F value:

Equation 13 ADC_0 (10-bit)

$$C_F > 2048 \bullet C_S$$

4.18 On-chip peripherals

4.18.1 Current consumption

Table 47. On-chip peripherals current consumption(1)

Symbol		C	Parameter	Conditions		Typical value(2)	Unit
$I_{DD\_BV(CAN)}$	CC	T	CAN (FlexCAN) supply current on V_{DD_BV}	Bitrate: 500 Kbyte/s	Total (static + dynamic) consumption: – FlexCAN in loop-back mode – XTAL at 8 MHz used as CAN engine clock source – Message sending period is 580 µs	8 * f_{periph} + 85	µA
				Bitrate: 125 Kbyte/s		8 * f_{periph} + 27	
$I_{DD\_BV(eMIOS)}$	CC	T	eMIOS supply current on V_{DD_BV}	Static consumption: – eMIOS channel OFF – Global prescaler enabled		29 * f_{periph}	µA
				Dynamic consumption: – It does not change varying the frequency (0.003 mA)		3	
$I_{DD\_BV(SCI)}$	CC	T	SCI (LINFlex) supply current on V_{DD_BV}	Total (static + dynamic) consumption: – LIN mode – Baudrate: 20 Kbyte/s		5 * f_{periph} + 31	µA
$I_{DD\_BV(SPI)}$	CC	T	SPI (DSPI) supply current on V_{DD_BV}	Ballast static consumption (only clocked)		1	µA
				Ballast dynamic consumption (continuous communication): – Baudrate: 2 Mbit/s – Transmission every 8 µs – Frame: 16 bits		16 * f_{periph}	
I_{DD_BV} (ADC_0/ADC_1)	CC	T	ADC_0/ADC_1 supply current on V_{DD_BV}	V_{DD} = 5.5 V	Ballast static consumption (no conversion)(3)	41 * f_{periph}	µA
					Ballast dynamic consumption (continuous conversion)(3)	46 * f_{periph}	
$I_{DD\_HV\_ADC0}$	CC	T	ADC_0 supply current on $V_{DD\_HV\_ADC0}$	V_{DD} = 5.5 V	Analog static consumption (no conversion)	200	µA
					Analog dynamic consumption (continuous conversion)	3	mA
$I_{DD\_HV\_ADC1}$	CC	T	ADC_1 supply current on $V_{DD\_HV\_ADC1}$	V_{DD} = 5.5 V	Analog static consumption (no conversion)	300 * f_{periph}	µA
					Analog dynamic consumption (continuous conversion)	4	mA